

#### **Description**

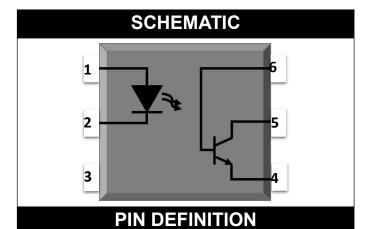
The 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38,H11A1, H11A2, H11A3, H11A4, H11A5 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector in a plastic DIP6 package with different lead forming options.

#### **Features**

- High isolation 5000 VRMS
- DC input with transistor output
- Operating temperature range 55 °C to 110 °C
- RoHS & REACH Compliance
- MSL class 1
- Regulatory Approvals
  - UL UL1577
  - VDE EN60747-5-5(VDE0884-5)
  - CQC GB4943.1, GB8898
  - cUL- CSA Component Acceptance
     Service Notice No. 5A

#### **Applications**

- Sequence controller
- Telephone/FAX
- System appliances, measuring instrument
- Programmable logic controller



1.Anode 6.Base 2.Cathode 5.Collector

3.NC 4.Emitter

# PACKAGE OUTLINE



DIP6, DC Input, Photo Transistor Coupler

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	VALUE	UNIT	NOTE		
INPUT						
Forward Current	I <sub>F</sub>	50	mA			
Peak Forward Current(t=10µs)	I <sub>FM</sub>	1	Α	1		
Reverse Voltage	V <sub>R</sub>	6	V			
Power Dissipation(TA=25°C)	P <sub>D</sub>	70	mW			
OU	TPUT					
Collector - Emitter Voltage	V <sub>CEO</sub>	80	V			
Collector-Base Breakdown Voltage	V <sub>CBO</sub>	80	V			
Emitter - Collector Voltage	V <sub>ECO</sub>	7	V			
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	7	V			
Collector Current	Ic	80	mA			
Power Dissipation(TA=25°C)	Pc	150	mW			
COMMON						
Total Power Dissipation	Ptot	200	mW			
Isolation Voltage	Viso	5000	Vrms	2		
Operating Temperature	Topr	-55~+110	°C			
Storage Temperature	Tstg	-55~+110	°C			
Soldering Temperature	Tsol	260	°C			

Note 1. AC For 1 Minute, R.H. =  $40 \sim 60\%$ 

Note 2. For 10 seconds



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ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C									
PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT	TEST CONDITION	NOTE		
	INPUT								
Forward Voltage	$V_{F}$	-	1.24	1.4	V	IF=10mA			
Reverse Current	$I_{R}$	-	-	10	μΑ	VR=6V			
Input Capacitance	Cin	-	30	-	pF	V=0, f=1kHz			
	OUTPUT								
Collector Dark Current	I <sub>CEO</sub>	-	-	50	nA	VCE=10V, IF=0			
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	80	-	-	V	IC=1mA, IF=0			
Emitter-Collector Breakdown Voltage	$BV_ECO$	7	-	-	V	IE=0.1mA, IF=0			
Collector-Base Breakdown	BV <sub>CBO</sub>	80	-	-	V	IC= 0.1mA, IF=0			
Emitter-Base Breakdown	BV <sub>EBO</sub>	7	_	-	V	IE= 0.1mA , IF=0			



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#### 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5

## DIP6, DC Input, Photo Transistor Coupler

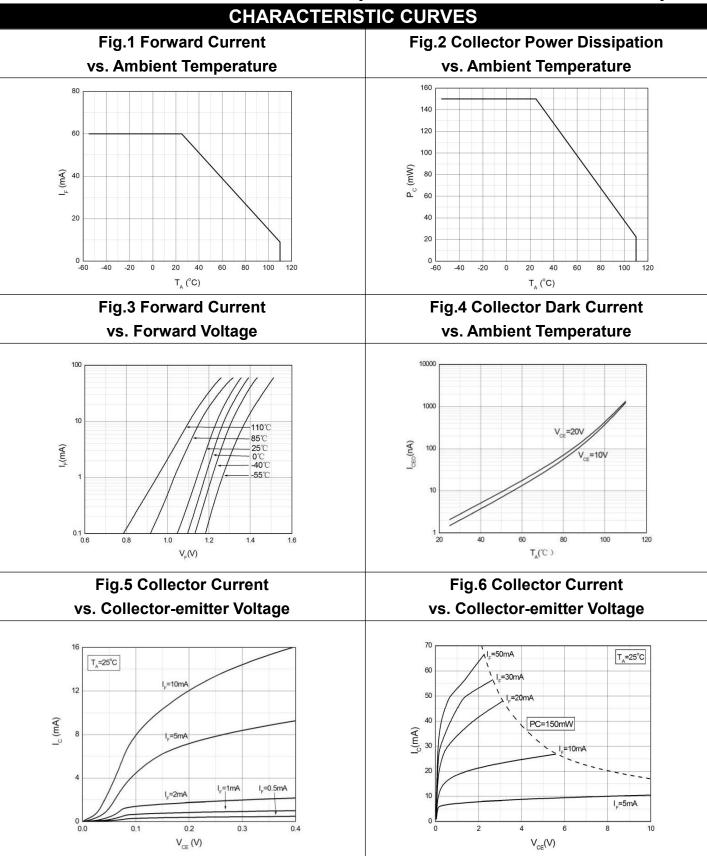
TRANSFER CHARACTERISTICS							
4N35, 4N36, 4N37			100				
Current Transfer Ratio	CTR	4N25,4N26, 4N38	100	-	-		
		H11A2, H11A3	20	-	-	%	
		4N27, 4N28,H11A4	10				IF=10mA, VCE=10V
		H11A1	50	-			
		H11A5	30	-		_	
		4N35,4N36,4N37	-	-	0.3		IF= 10mA, IC= 0.5mA
		4N38	_	-	1.0		IF= 20mA, IC= 4mA
Collector-Emitt		4N25,4N26,	_	_	1.0		11 - 2011A, 10- 411A
er	V <sub>CE(sat)</sub>	4N27,4N28	-	-	0.5	V	IF= 50mA, IC= 2mA
Saturation		H11A1,H11A2,				-	
Voltage		H11A3,H11A4,	_	_	0.4	4	IF= 10mA, IC= 0.5mA
		H11A5					
Isolation	R <sub>IO</sub>		10^12	10^14	-	Ω	V <sub>IO</sub> =500Vdc.
Resistance			10 12	10 17 22	32	V 10-300 V UC.	
Floating	C <sub>IO</sub>		- (	0.2 1	1	1 pF	V=0, f=1MHz
Capacitance				0.2	•	β.	·
Cut-off		fc	_	6	_	kHz	VCE=5V, IC=2mA
Frequency		T				IXI IZ	RL=100Ω,-3dB
	t <sub>on</sub>	4N25,4N26,4N27,	-	3	15	15 -	
		4N28,H11A1,					IF= 10mA, VCC=
Turn On Time		H11A2,H11A3,					10V, RL= 100Ω
		H11A4,H11A5					
		4N35,4N36,4N37,	_	10	12	-	Ic= 2mA, VCC= 10V,
		4N38					RL= 100Ω
Turn Off Time	t <sub>off</sub>	4N25,4N26,4N27,	-		16	-	
		4N284N28,H11A1,		3			IF= 10mA, VCC=
		H11A2,H11A3,					10V, RL= 100Ω
	J.,	H11A4,H11A5					
		4N35,4N36,4N37, 4N38	-	9	12	_	Ic= 10mA, VCC= 10V, RL= 100Ω

Release Date: 2024/08/17



Document No: DWI-10161

#### DIP6, DC Input, Photo Transistor Coupler



Rev: A00

H11A1, H11A2, H11A3, H11A4, H11A5

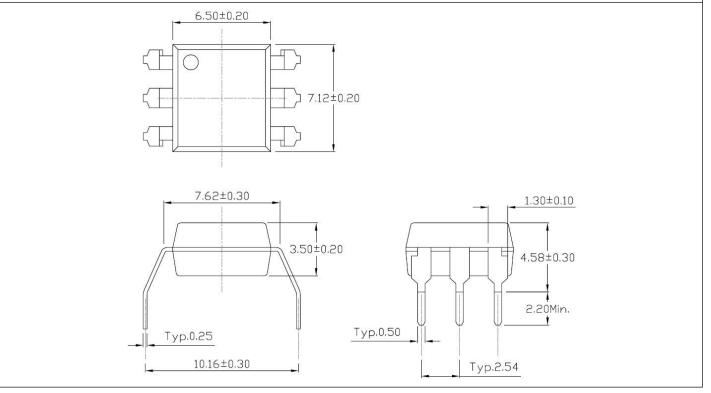
## DIP6, DC Input, Photo Transistor Coupler

#### **CHARACTERISTIC CURVES** Fig.7 Normalized Current Transfer Ratio Fig.8 Normalized Current Transfer Ratio vs. Forward Current vs. Ambient Temperature V<sub>CF</sub>=10V V\_=10V T\_=25°C Normalized to T<sub>A</sub>=25℃ Normalized I\_=10mA 1.0 1.1 I\_=5mA 1.0 Normalized CTR Normalized CTR 0.9 =10m/ 0.8 I\_=20mA 0.7 0.6 0.6 50 60 -20 40 80 -60 20 100 $I_{E}(mA)$ $T_{A}(^{\circ}\mathbb{C})$ Fig.9 Current Transfer Ratlo(Unsaturated) vs Fig.10 Switching Time **Base-Emitter Resistance** vs. Load Resistance 16 1.0 V<sub>CF</sub>=10V V<sub>CE</sub>=10V I<sub>C</sub>=10mA Normalized to R<sub>BE</sub>=Open 14 Normalized Curent Trnsfer Ratio CTR T₄=25°C 12 Response Time(us) \_=10mA I\_=20mA L=5mA 0.0 1000 0.2 0.4 0.6 0.8 1.0 Base-Emitter Resistance $R_{pg}(K\Omega)$ Load Resistance(KΩ)



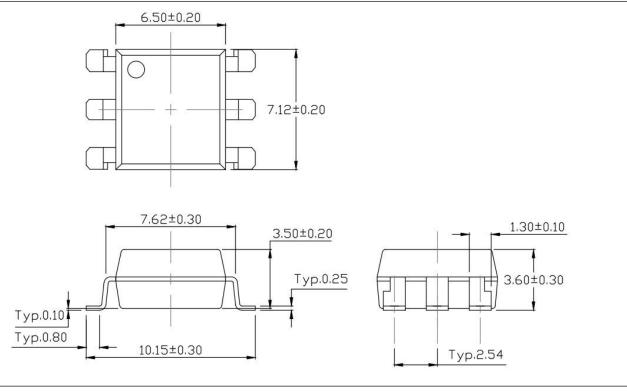
# PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated) **Standard DIP – Through Hole (DIP Type)** 6.50±0.20 7.12±0.20 7.62±0.30 1.30±0.10 3.50±0.20 4.50±0.30 Typ.2.80 Typ.0.50 Typ.0.25 5°~15° Typ.2.54 7.62~9.50

#### Gullwing (400mil) Lead Forming – Through Hole (M Type)





# PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated) **Surface Mount Lead Forming (S Type)** 6.50±0.20 □ 7.12±0.20 7.62±0.30 1.30±0.10 3.50±0.<u>2</u>0 4.30±0.30 Typ.0.25 Typ.0.80 Тур.0.50 Typ.0.80 10.15±0.30 Typ.2.54 Surface Mount (Low Profile) Lead Forming (SL Type) 6.50±0.20





# DIP6, DC Input, Photo Transistor Coupler

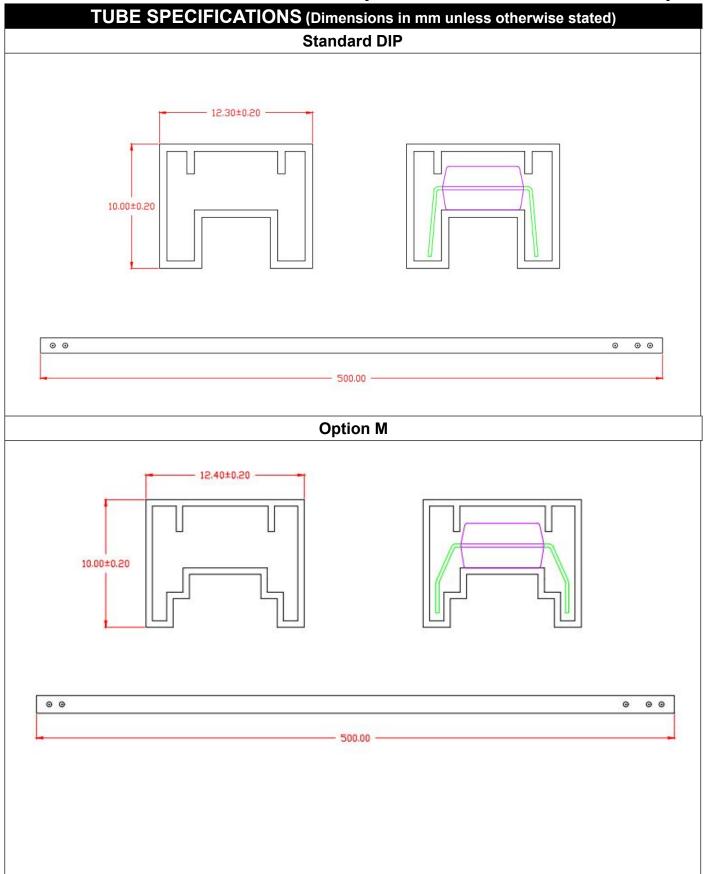
# Recommended Solder Mask (Dimensions in mm unless otherwise stated) Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming 1.60 1.80 6.88 2.54 10.75 **Surface Mount (Gullwing) Lead Forming** 1.60 1.00 6.08 2.54 12,40



#### 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, www.tdled.com

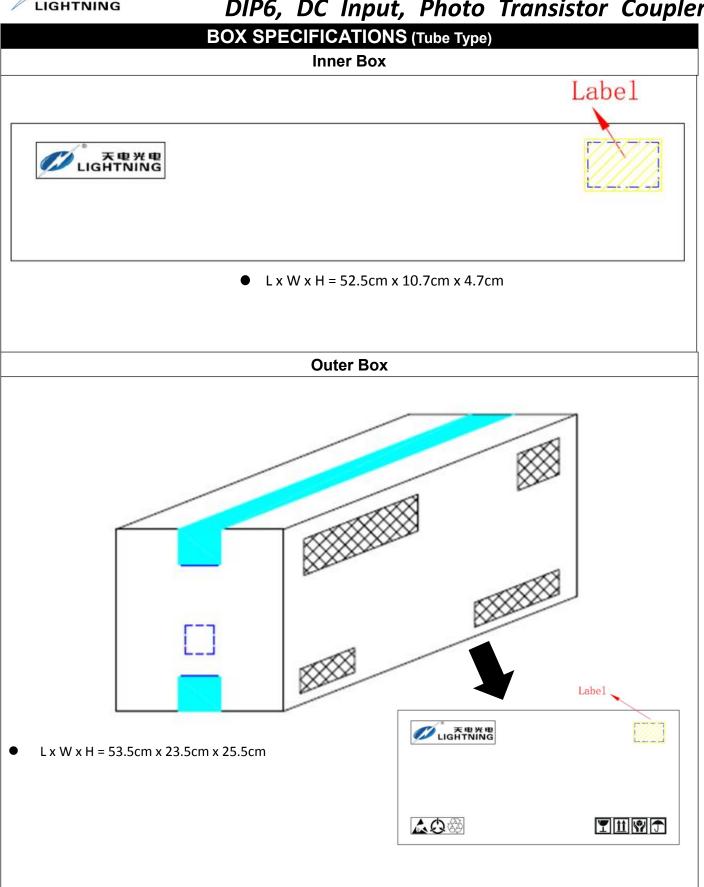
H11A1, H11A2, H11A3, H11A4, H11A5

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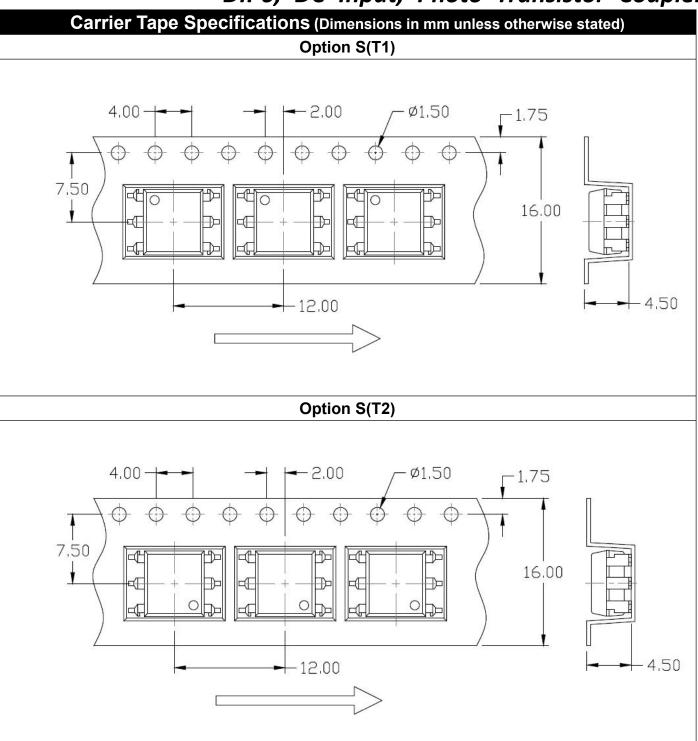


# DIP6, DC Input, Photo Transistor Coupler



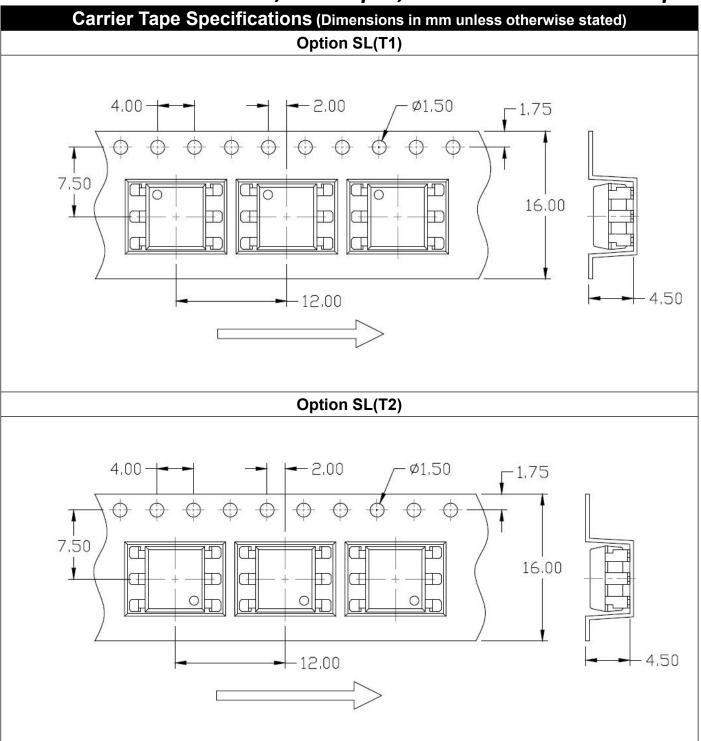


DIP6, DC Input, Photo Transistor Coupler



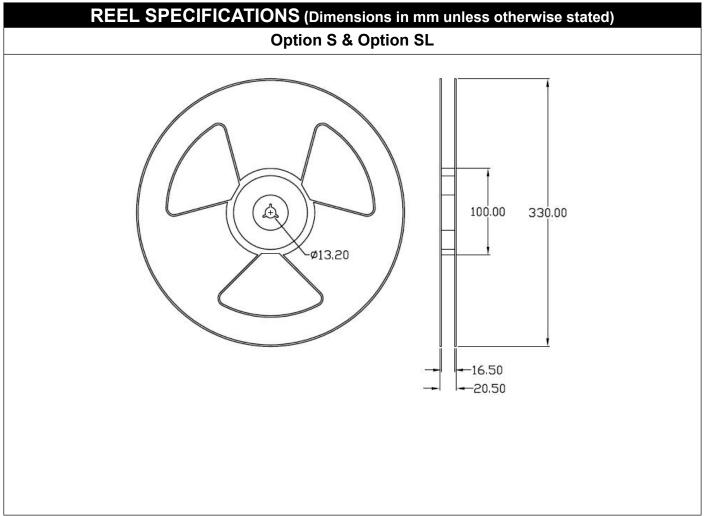


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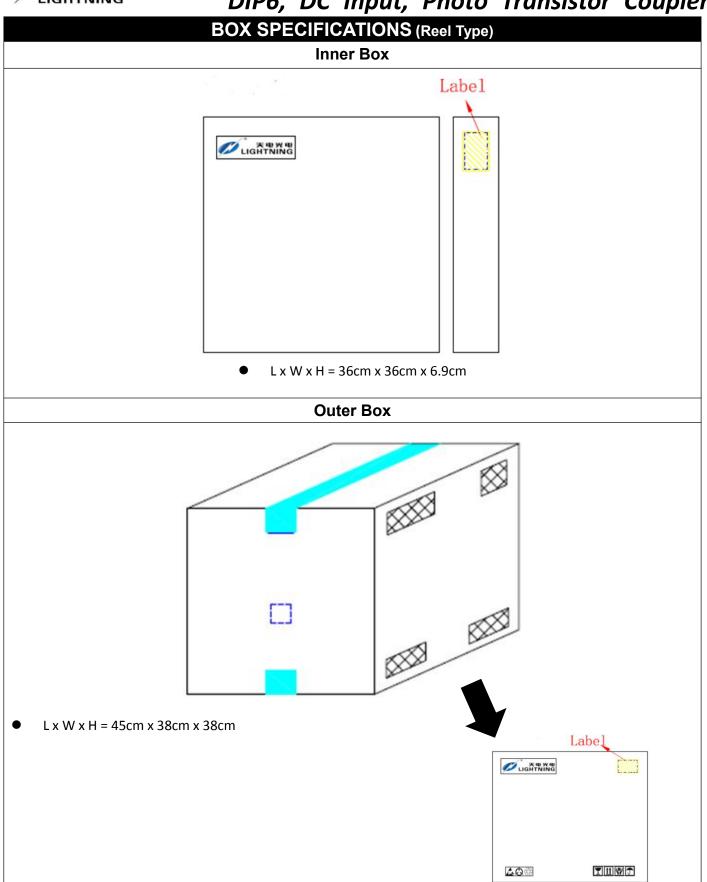




## DIP6, DC Input, Photo Transistor Coupler



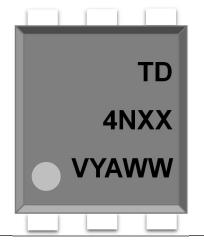
## DIP6, DC Input, Photo Transistor Coupler



#### ORDERING AND MARKING INFORMATION

#### MARKING INFORMATION

4NXX



TD : Company Abbr.

: Part Number & Rank

V : VDE Option Y : Fiscal Year

A : Manufacturing Code

WW : Work Week

#### ORDERING INFORMATION

# 4NXX(Y)(Z)-GV

TD - Company Abbr.

4NXX – Part Number and Rank

(XX=25/26/27/28/35/36/37/38)

Y – Lead Form Option

(M/S/SL/None)

Z – Tape and Reel Option (T1/T2)

G – Material Option

(G: Green, None: Non-Green)

V – VDE Option (V or None)

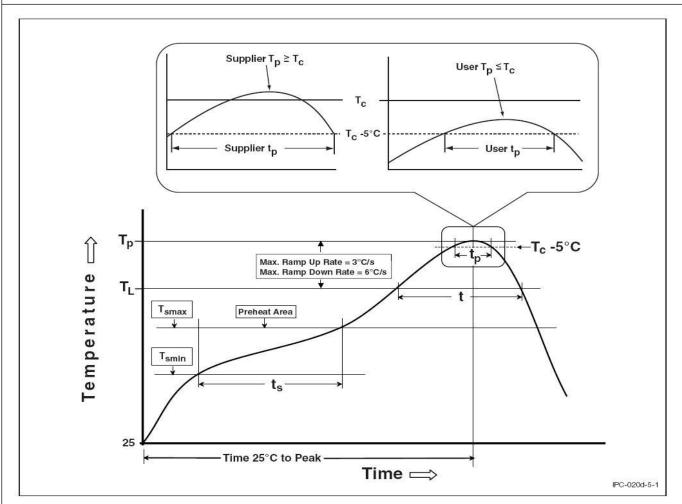
#### LABEL INFORMATION



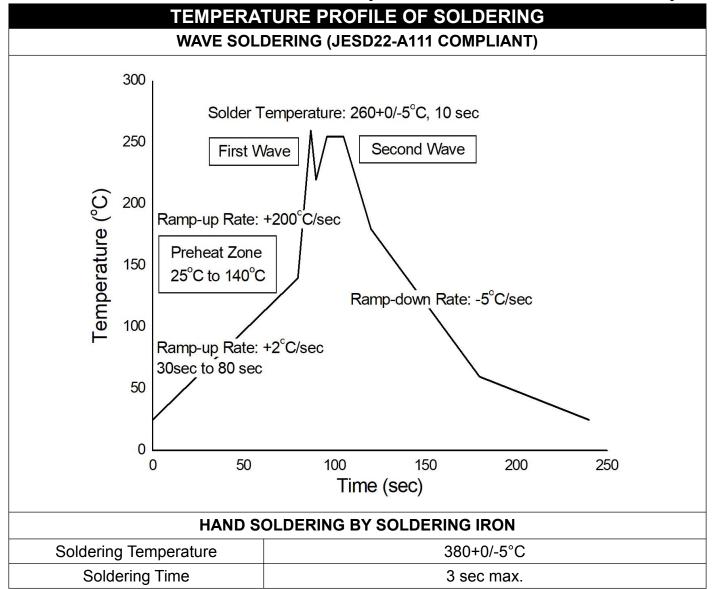
PACKING QUANTITY					
Option	Quantity	Quantity – Inner box	Quantity – Outer box		
None	65 Units/Tube	32 Tubes/Inner box	10 Inner box/Outer box = 20.8k Units		
M	65 Units/Tube	32 Tubes/Inner box	10 Inner box/Outer box = 20.8k Units		
S(T1)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units		
S(T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units		
SL(T1)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units		
SL(T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units		

#### **REFLOW INFORMATION**

#### **REFLOW PROFILE**



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile		
Temperature Min. (Tsmin)	100	150°C		
Temperature Max. (Tsmax)	150	200°C		
Time (ts) from (Tsmin to Tsmax)	60-120 seconds	60-120 seconds		
Ramp-up Rate (tL to tP)	3°C/second max.	3°C/second max.		
Liquidous Temperature (TL)	183°C	217°C		
Time (tL) Maintained Above (TL)	60 – 150 seconds	60 – 150 seconds		
Peak Body Package Temperature	235°C +0°C / -5°C	260°C +0°C / -5°C		
Time (tP) within 5°C of 260°C	20 seconds	30 seconds		
Ramp-down Rate (TP to TL)	6°C/second max	6°C/second max		
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.		



- One time soldering is recommended for all soldering method.
- Do not solder more than three times for IR reflow soldering.



#### DIP6, DC Input, Photo Transistor Coupler

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- Please contact LIGHTNING sales agent for special application request.
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- Parameters provided in datasheets may vary in different applications and performance may vary
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